

Linfeng Lan

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Solution-Processed Quantum-Dots Light-Emitting Transistors With Equivalent Efficiency of Light-Emitting Diodes. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 521-524.	3.0	2
2	Effect of Head Groups in Self-Assembled Monolayer Passivation on Properties of InSnZnO Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 160-165.	3.0	3
3	Hybrid Elastic Organic Crystals that Respond to Aerial Humidity. <i>Angewandte Chemie - International Edition</i> , 2022, 61, .	13.8	44
4	Organic Single-Crystal Actuators and Waveguides that Operate at Low Temperatures. <i>Advanced Materials</i> , 2022, 34, e2200471.	21.0	34
5	Gate Dielectric Treated by Self-Assembled Monolayers (SAMs) to Enhance the Performance of InSnZnO Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 2398-2403.	3.0	8
6	Packing-Dependent Mechanical Properties of Schiff Base Crystals. <i>Crystal Growth and Design</i> , 2022, 22, 3435-3441.	3.0	15
7	Remote and precise control over morphology and motion of organic crystals by using magnetic field. <i>Nature Communications</i> , 2022, 13, 2322.	12.8	34
8	The Effect of the Charge Transfer Transition of the Tetravalent Terbium on the Photostability of Oxide Thin-Film Transistors. <i>Advanced Electronic Materials</i> , 2022, 8, .	5.1	7
9	Polymer-Coated Organic Crystals with Solvent-Resistant Capacity and Optical Waveguiding Function. <i>Angewandte Chemie</i> , 2021, 133, 11383-11387.	2.0	7
10	Polymer-Coated Organic Crystals with Solvent-Resistant Capacity and Optical Waveguiding Function. <i>Angewandte Chemie - International Edition</i> , 2021, 60, 11283-11287.	13.8	28
11	Influence of Hydrogen Ions on the Performance of Thin-Film Transistors with Solution-Processed AlO _x Gate Dielectrics. <i>Applied Sciences (Switzerland)</i> , 2021, 11, 4393.	2.5	2
12	The effect of charge transfer transition on the photostability of lanthanide-doped indium oxide thin-film transistors. <i>Communications Materials</i> , 2021, 2, .	6.9	18
13	Inkjet-Printed Full-Color Matrix Quasi-Two-Dimensional Perovskite Light-Emitting Diodes. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 41773-41781.	8.0	35
14	Effect of Bandgap Widening on Negative-Bias Illumination Stress Stability of Oxide Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 4450-4454.	3.0	5
15	Effect of Sc ₂ O ₃ Passivation Layer on the Electrical Characteristics and Stability of InSnZnO Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 4956-4961.	3.0	10
16	InSnZnO Thin-Film Transistors With Nitrogenous Self-Assembled Multilayers Passivation. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 5612-5617.	3.0	5
17	Effect of Self-Assembled Monolayers (SAMs) as Surface Passivation on the Flexible a-InSnZnO Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 3157-3162.	3.0	20
18	Self-Assembled Monolayers (SAMs)/Al ₂ O ₃ Double Layer Passivated InSnZnO Thin-Film Transistor. <i>IEEE Access</i> , 2020, 8, 101834-101839.	4.2	8

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19	High-performance capacitive strain sensors with highly stretchable vertical graphene electrodes. <i>Journal of Materials Chemistry C</i> , 2020, 8, 5541-5546.	5.5	39
20	Highly efficient and stable hybrid quantum-dot light-emitting field-effect transistors. <i>Materials Horizons</i> , 2020, 7, 2439-2449.	12.2	4
21	Inkjet-Printed Top-Gate Thin-Film Transistors Based on InGaSnO Semiconductor Layer with Improved Etching Resistance. <i>Coatings</i> , 2020, 10, 425.	2.6	4
22	Inkjet-Printed Oxide Thin-Film Transistors Based on Nanopore-Free Aqueous-Processed Dielectric for Active-Matrix Quantum-Dot Light-Emitting Diode Displays. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 28052-28059.	8.0	16
23	Controllably realizing elastic/plastic bending based on a room-temperature phosphorescent waveguiding organic crystal. <i>Chemical Science</i> , 2019, 10, 227-232.	7.4	112
24	Reduction of sixth-order radial force by harmonic current control and its application to EPS motors. <i>Electrical Engineering in Japan (English Translation of Denki Gakkai Ronbunshi)</i> , 2019, 209, 45-56.	0.4	1
25	Ultrasensitive and Highly Stretchable Multifunctional Strain Sensors with Timbre Recognition Ability Based on Vertical Graphene. <i>Advanced Functional Materials</i> , 2019, 29, 1907151.	14.9	59
26	Approaching subthreshold-swing limit for thin-film transistors by using a giant-dielectric-constant gate dielectric. <i>RSC Advances</i> , 2019, 9, 27117-27124.	3.6	8
27	High-Performance Amorphous Zinc-Tin Oxide Thin-Film Transistors With Low Tin Concentration. <i>IEEE Journal of the Electron Devices Society</i> , 2019, 7, 632-637.	2.1	5
28	Aqueous solution-processed, self-flattening AlOx:Y dielectrics for fully-transparent thin-film transistors. <i>Ceramics International</i> , 2019, 45, 15883-15891.	4.8	5
29	Improving Negative-Bias-Temperature-Stress Stability for Thin-Film Transistors by Doping Mg Into ScInO Semiconductor. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2620-2623.	3.0	2
30	Solution-processed metal-oxide thin-film transistors: a review of recent developments. <i>Nanotechnology</i> , 2019, 30, 312001.	2.6	78
31	High-performance CdScInO thin-film transistors and their stability improvement under negative bias (illumination) temperature stress. <i>Journal of Materials Chemistry C</i> , 2019, 7, 13960-13965.	5.5	3
32	Inkjet-Printed Self-Aligned Short-Channel Metal-Oxide Thin-Film Transistors Based on Coffee Stripe Dewetting Method. <i>IEEE Electron Device Letters</i> , 2019, 40, 228-231.	3.9	4
33	Fully Printed Top-Gate Metal Oxide Thin-Film Transistors Based on Scandium-Zirconium-Oxide Dielectric. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 445-450.	3.0	20
34	High-Performance and Flexible Neodymium-Doped Oxide Semiconductor Thin-Film Transistors With Copper Alloy Bottom-Gate Electrode. <i>IEEE Electron Device Letters</i> , 2018, 39, 839-842.	3.9	15
35	Design, Properties, and TFT Application of Solution-Processed InGaCdO Thin Films. <i>Physica Status Solidi - Rapid Research Letters</i> , 2018, 12, 1800034.	2.4	7
36	Photoluminescence and Electrical Properties study of ITO-stabilized ZnO Thin-Film Transistors with different annealing temperatures. <i>Digest of Technical Papers SID International Symposium</i> , 2018, 49, 520-523.	0.3	1

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37	Effects of annealing temperature on properties of InSnZnO thin film transistors prepared by Co-sputtering. RSC Advances, 2018, 8, 34817-34822.	3.6	39
38	InSnZnO Thin-Film Transistors With Vapor- Phase Self-Assembled Monolayer as Passivation Layer. IEEE Electron Device Letters, 2018, 39, 1680-1683.	3.9	18
39	P: Solution‑processed metal oxide semiconductors fabricated with oxygen radical assisting perchlorate aqueous precursors through a new low‑temperature reaction route. Digest of Technical Papers SID International Symposium, 2018, 49, 547-550.	0.3	0
40	Aqueous Solution Induced High-Dielectric-Constant AlO ₃ :Y Films for Thin-Film Transistor Applications. Journal of Nanoscience and Nanotechnology, 2018, 18, 7566-7572.	0.9	5
41	Trifluoromethyl-Substituted Large Band-Gap Polytriphenylamines for Polymer Solar Cells with High Open-Circuit Voltages. Polymers, 2018, 10, 52.	4.5	1
42	Solution-processed Ga‑Cd‑O thin-films with tunable bandgaps and their transistors. Journal Physics D: Applied Physics, 2018, 51, 335101.	2.8	4
43	High-Performance, Solution-Processed Quantum Dot Light-Emitting Field-Effect Transistors with a Scandium-Incorporated Indium Oxide Semiconductor. ACS Nano, 2018, 12, 4624-4629.	14.6	25
44	High-Performance Organic Field-Effect Transistors Fabricated Based on a Novel Ternary ‑Conjugated Copolymer. ACS Applied Materials & Interfaces, 2017, 9, 7315-7321.	8.0	27
45	Low temperature, solution-processed ambipolar field-effect transistors based on polymer/self-assembled monolayer modified InOx hybrid structures for balanced hole and electron mobilities exceeding 1‑1. Organic Electronics, 2017, 43, 162-166.	2.6	7
46	All Inkjet-Printed Metal-Oxide Thin-Film Transistor Array with Good Stability and Uniformity Using Surface-Energy Patterns. ACS Applied Materials & Interfaces, 2017, 9, 8194-8200.	8.0	98
47	A room temperature strategy towards enhanced performance and bias stability of oxide thin film transistor with a sandwich structure channel layer. Applied Physics Letters, 2017, 110, .	3.3	11
48	A solution-processed and low threshold voltage p-type small molecule based on indolocarbazole- and benzothiophene-fused rings. Dyes and Pigments, 2017, 144, 32-40.	3.7	12
49	Island‑Like AZO/Al ₂ O ₃ Bilayer Channel Structure for Thin Film Transistors. Advanced Materials Interfaces, 2017, 4, 1700063.	3.7	10
50	High Mobility Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistor by Aluminum Oxide Passivation Layer. IEEE Electron Device Letters, 2017, 38, 879-882.	3.9	54
51	Low-temperature, high-mobility, solution-processed metal oxide semiconductors fabricated with oxygen radical assisted perchlorate aqueous precursors. Chemical Communications, 2017, 53, 6436-6439.	4.1	7
52	Highly conductive AZO thin films obtained by rationally optimizing substrate temperature and oxygen partial pressure. Molecular Crystals and Liquid Crystals, 2017, 644, 190-196.	0.9	4
53	Solution-processed high-mobility neodymium-substituted indium oxide thin-film transistors formed by facile patterning based on aqueous precursors. Applied Physics Letters, 2017, 110, .	3.3	27
54	Stable ambipolar organic‑inorganic heterojunction field-effect transistors and inverters with Cytop interlayer. RSC Advances, 2017, 7, 5966-5969.	3.6	20

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55	High-performance thin-film transistors with solution-processed ScInO channel layer based on environmental friendly precursor. Journal Physics D: Applied Physics, 2017, 50, 385108.	2.8	11
56	Direct patterning of silver electrodes with 2.4 μ m channel length by piezoelectric inkjet printing. Journal of Colloid and Interface Science, 2017, 487, 68-72.	9.4	30
57	Polystyrenesulfonate Dispersed Dopamine with Unexpected Stable Semiquinone Radical and Electrochemical Behavior: A Potential Alternative to PEDOT:PSS. ACS Sustainable Chemistry and Engineering, 2017, 5, 460-468.	6.7	17
58	A study on the bottom-gate ITO-stabilized ZnO thin-film transistors. , 2017, , .		0
59	Effect of Intrinsic Stress on Structural and Optical Properties of Amorphous Si-Doped SnO ₂ Thin-Film. Materials, 2017, 10, 24.	2.9	15
60	All-Aluminum Thin Film Transistor Fabrication at Room Temperature. Materials, 2017, 10, 222.	2.9	11
61	Effect of Post Treatment For Cu-Cr Source/Drain Electrodes on a-IGZO TFTs. Materials, 2016, 9, 623.	2.9	20
62	Letter : Solution-processed flexible zinc-tin oxide thin-film transistors on ultra-thin polyimide substrates. Journal of the Society for Information Display, 2016, 24, 211-215.	2.1	3
63	High-mobility flexible thin-film transistors with a low-temperature zirconium-doped indium oxide channel layer. Physica Status Solidi - Rapid Research Letters, 2016, 10, 493-497.	2.4	13
64	High-performance back-channel-etched thin-film transistors with amorphous Si-incorporated SnO ₂ active layer. Applied Physics Letters, 2016, 108, .	3.3	25
65	A novel nondestructive testing method for amorphous Si-Sn-O films. Journal Physics D: Applied Physics, 2016, 49, 505102.	2.8	18
66	High-mobility flexible thin-film transistors with zirconium-doped indium oxide channel layer. , 2016, , .		0
67	Low-temperature, high-stability, flexible thin-film transistors with a novel Sc _x In _{1-x} O ₃ semiconductor. Journal Physics D: Applied Physics, 2016, 49, 24LT01.	2.8	9
68	Thin-Film Transistors With Neodymium-Incorporated Indium-Zinc-Oxide Semiconductors. IEEE Transactions on Electron Devices, 2016, 63, 1916-1920.	3.0	12
69	Wide bandgap dithienobenzodithiophene-based π -conjugated polymers consisting of fluorinated benzotriazole and benzothiadiazole for polymer solar cells. Journal of Materials Chemistry C, 2016, 4, 4719-4727.	5.5	34
70	Effects of Rare-Earth Element Dopants in High-Mobility InO _x -Based Thin-Film Transistors. IEEE Electron Device Letters, 2016, 37, 1139-1142.	3.9	12
71	Low-temperature synthesis and electronic transport of topological insulator SmB ₆ nanowires. CrystEngComm, 2016, 18, 7934-7939.	2.6	18
72	Coffee-Ring Defined Short Channels for Inkjet-Printed Metal Oxide Thin-Film Transistors. ACS Applied Materials & Interfaces, 2016, 8, 19643-19648.	8.0	54

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73	High-Mobility and Good-Stability Thin-Film Transistors With Scandium-Substituted Indium Oxide Semiconductors. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 4315-4319.	3.0	11
74	Flexible All-organic, All-solution Processed Thin Film Transistor Array with Ultrashort Channel. <i>Scientific Reports</i> , 2016, 6, 29055.	3.3	48
75	High-mobility ZrInO thin-film transistor prepared by an all-DC-sputtering method at room temperature. <i>Scientific Reports</i> , 2016, 6, 25000.	3.3	16
76	Role of Evaporated Silver Nanoparticles in Organic Field-Effect Transistor: Electrical Effects and Dependence on the Size. <i>Journal of Physical Chemistry C</i> , 2016, 120, 1847-1853.	3.1	8
77	Effects of pyridyl group orientations on the optoelectronic properties of regio-isomeric diketopyrrolopyrrole based π -conjugated polymers. <i>Journal of Materials Chemistry C</i> , 2016, 4, 2470-2479.	5.5	13
78	Facile patterning of amorphous indium oxide thin films based on a gel-like aqueous precursor for low-temperature, high performance thin-film transistors. <i>Journal of Materials Chemistry C</i> , 2016, 4, 2072-2078.	5.5	23
79	High-mobility thin film transistors with neodymium-substituted indium oxide active layer. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	30
80	Solution-processed indium-zinc-oxide thin-film transistors based on anodized aluminum oxide gate insulator modified with zirconium oxide. <i>RSC Advances</i> , 2015, 5, 51440-51445.	3.6	21
81	Efficient single-emitting layer hybrid white organic light-emitting diodes with low efficiency roll-off, stable color and extremely high luminance. <i>Journal of Industrial and Engineering Chemistry</i> , 2015, 30, 85-91.	5.8	20
82	Effects of flanked units on optoelectronic properties of diketopyrrolopyrrole based π -conjugated polymers. <i>Dyes and Pigments</i> , 2015, 123, 64-71.	3.7	17
83	Harnessing charge and exciton distribution towards extremely high performance: the critical role of guests in single-emitting-layer white OLEDs. <i>Materials Horizons</i> , 2015, 2, 536-544.	12.2	48
84	Effects of Nd in NdIn_3O_3 Semiconductors for Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2015, 62, 2226-2230.	3.0	13
85	High mobility flexible polymer thin-film transistors with an octadecyl-phosphonic acid treated electrochemically oxidized alumina gate insulator. <i>Journal of Materials Chemistry C</i> , 2015, 3, 7062-7066.	5.5	20
86	Effects of bridge units on the properties of indolo[3,2-b]carbazole-co-difluorobenzo[d][1,2,3]triazole based π -conjugated copolymers. <i>Organic Electronics</i> , 2015, 23, 17-27.	2.6	19
87	Flexible organic field-effect transistors with high-reliability gate insulators prepared by a room-temperature, electrochemical-oxidation process. <i>RSC Advances</i> , 2015, 5, 15695-15699.	3.6	16
88	InGaZnO Thin-Film Transistors Modified by Self-Assembled Monolayer With Different Alkyl Chain Length. <i>IEEE Electron Device Letters</i> , 2015, 36, 687-689.	3.9	15
89	High-performance hybrid white organic light-emitting diodes employing p-type interlayers. <i>Journal of Industrial and Engineering Chemistry</i> , 2015, 27, 240-244.	5.8	19
90	Regulating charges and excitons in simplified hybrid white organic light-emitting diodes: The key role of concentration in single dopant host-guest systems. <i>Organic Electronics</i> , 2014, 15, 2616-2623.	2.6	32

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91	Studies on $\text{NdxIn}_{1-x}\text{O}_3$ semiconducting thin films prepared by rf magnetron sputtering. Applied Physics Letters, 2014, 105, .	3.3	21
92	InGaZnO thin-film transistors with back channel modification by organic self-assembled monolayers. Applied Physics Letters, 2014, 104, .	3.3	41
93	Simplified hybrid white organic light-emitting diodes with efficiency/efficiency roll-off/color rendering index/color-stability trade-off. Physica Status Solidi - Rapid Research Letters, 2014, 8, 719-723.	2.4	14
94	Effects of Solvent Treatment on the Characteristics of InGaZnO Thin-Film Transistors. ECS Journal of Solid State Science and Technology, 2014, 3, Q3081-Q3084.	1.8	8
95	Investigation and optimization of each organic layer: A simple but effective approach towards achieving high-efficiency hybrid white organic light-emitting diodes. Organic Electronics, 2014, 15, 926-936.	2.6	36
96	Low Band-Gap Conjugated Polymers with Strong Interchain Aggregation and Very High Hole Mobility Towards Highly Efficient Thick-Film Polymer Solar Cells. Advanced Materials, 2014, 26, 2586-2591.	21.0	375
97	Performance improvement of oxide thin-film transistors with a two-step-annealing method. Solid-State Electronics, 2014, 91, 9-12.	1.4	22
98	Very-High Color Rendering Index Hybrid White Organic Light-Emitting Diodes with Double Emitting Nanolayers. Nano-Micro Letters, 2014, 6, 335-339.	27.0	34
99	The effect of spacer in hybrid white organic light emitting diodes. Science Bulletin, 2014, 59, 3090-3097.	1.7	14
100	A flexible AMOLED display on the PEN substrate driven by oxide thin-film transistors using anodized aluminium oxide as dielectric. Journal of Materials Chemistry C, 2014, 2, 1255-1259.	5.5	84
101	Extremely stable-color flexible white organic light-emitting diodes with efficiency exceeding $100 \text{ lm W}^{-1} \text{ sr}^{-1} \text{ cd}^{-1}$. Journal of Materials Chemistry C, 2014, 2, 9836-9841.	5.5	48
102	Simultaneous achievement of low efficiency roll-off and stable color in highly efficient single-emitting-layer phosphorescent white organic light-emitting diodes. Journal of Materials Chemistry C, 2014, 2, 5870-5877.	5.5	23
103	Hybrid white organic light emitting diodes with low efficiency roll-off, stable color and extreme brightness. Journal of Luminescence, 2014, 151, 161-164.	3.1	17
104	Efficient hybrid white organic light-emitting diodes with extremely long lifetime: the effect of n-type interlayer. Scientific Reports, 2014, 4, 7198.	3.3	42
105	Investigation on spacers and structures: A simple but effective approach toward high-performance hybrid white organic light emitting diodes. Synthetic Metals, 2013, 184, 5-9.	3.9	16
106	Solution-processed efficient CdTe nanocrystal/CBD-CdS hetero-junction solar cells with ZnO interlayer. Journal of Nanoparticle Research, 2013, 15, 1.	1.9	19
107	Comprehensive Study on the Electron Transport Layer in Blue Fluorescent Organic Light-Emitting Diodes. ECS Journal of Solid State Science and Technology, 2013, 2, R258-R261.	1.8	24
108	Low-Roughness and Easily-Etched Transparent Conducting Oxides with a Stack Structure of ITO and IZO. ECS Journal of Solid State Science and Technology, 2013, 2, R245-R248.	1.8	3

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109	Enhancement of bias and illumination stability in thin-film transistors by doping InZnO with wide-band-gap Ta ₂ O ₅ . Applied Physics Letters, 2013, 102, .	3.3	46
110	High-Performance Hybrid White Organic Light-Emitting Diodes Comprising Ultrathin Blue and Orange Emissive Layers. Applied Physics Express, 2013, 6, 122101.	2.4	22
111	Role of Rare Earth Ions in Anodic Gate Dielectrics for Indium-Zinc-Oxide Thin-Film Transistors. Journal of the Electrochemical Society, 2012, 159, H502-H506.	2.9	39
112	Impact of Deposition Temperature of the Silicon Oxide Passivation on the Performance of Indium Zinc Oxide Thin-Film Transistors. Japanese Journal of Applied Physics, 2012, 51, 076501.	1.5	9
113	A low-cost low-temperature thin-film transistor backplane based on oxide semiconductor. Journal of the Society for Information Display, 2012, 20, 175-177.	2.1	6
114	Low-Voltage High-Stability Indium-Zinc Oxide Thin-Film Transistor Gated by Anodized Neodymium-Doped Aluminum. IEEE Electron Device Letters, 2012, 33, 827-829.	3.9	54
115	High reliability amorphous oxide semiconductor thin-film transistors gated by buried thick aluminum. Physica Status Solidi - Rapid Research Letters, 2012, 6, 403-405.	2.4	9
116	High Efficiency and High V_{oc} Inverted Polymer Solar Cells Based on a Low-Lying HOMO Polycarbazole Donor and a Hydrophilic Polycarbazole Interlayer on ITO Cathode. Journal of Physical Chemistry C, 2012, 116, 14188-14198.	3.1	105
117	Inverted polymer solar cells with a solution-processed zinc oxide thin film as an electron collection layer. Science China Chemistry, 2012, 55, 755-759.	8.2	14
118	Impact of Deposition Temperature of the Silicon Oxide Passivation on the Performance of Indium Zinc Oxide Thin-Film Transistors. Japanese Journal of Applied Physics, 2012, 51, 076501.	1.5	19
119	Influence of source and drain contacts on the properties of the indium-zinc oxide thin-film transistors based on anodic aluminum oxide gate dielectrics. Journal of Applied Physics, 2011, 110, .	2.5	30
120	P&C25: A 2.5-inch AMOLED Display Using InZnO Oxide TFTs with Anodized Al ₂ O ₃ Gate Insulator. Digest of Technical Papers SID International Symposium, 2011, 42, 1185-1187.	0.3	0
121	High-Performance Indium-Gallium-Zinc Oxide Thin-Film Transistors Based on Anodic Aluminum Oxide. IEEE Transactions on Electron Devices, 2011, 58, 1452-1455.	3.0	107
122	Tuning on threshold voltage of organic field-effect transistor with a copper oxide layer. Organic Electronics, 2011, 12, 429-434.	2.6	17
123	Gate bias stress stability under light irradiation for indium zinc oxide thin-film transistors based on anodic aluminium oxide gate dielectrics. Journal Physics D: Applied Physics, 2011, 44, 455102.	2.8	18
124	High performance indium-zinc-oxide thin-film transistors fabricated with a back-channel-etch-technique. Applied Physics Letters, 2011, 99, .	3.3	80
125	Solution-Processed Zinc Oxide Thin Film as a Buffer Layer for Polymer Solar Cells with an Inverted Device Structure. Journal of Physical Chemistry C, 2010, 114, 6849-6853.	3.1	198
126	Dipole-Induced Organic Field-Effect Transistor Gated by Conjugated Polyelectrolyte. Japanese Journal of Applied Physics, 2009, 48, 080206.	1.5	5

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127	Low-voltage, high-performance n-channel organic thin-film transistors based on tantalum pentoxide insulator modified by polar polymers. <i>Organic Electronics</i> , 2009, 10, 346-351.	2.6	32
128	Synthesis of Novel Conjugated Polyelectrolytes for Organic Field-Effect Transistors Gate Dielectric Materials. <i>Macromolecular Chemistry and Physics</i> , 2008, 209, 2504-2509.	2.2	10
129	Field effect transistor from individual trigonal Se nanowire. <i>Nanotechnology</i> , 2008, 19, 355201.	2.6	13
130	High-performance polymer heterojunction solar cells of a polysilfluorene derivative. <i>Applied Physics Letters</i> , 2008, 92, 033307.	3.3	446
131	Hybrid Elastic Organic Crystals that Respond to Aerial Humidity. <i>Angewandte Chemie</i> , 0, , .	2.0	12